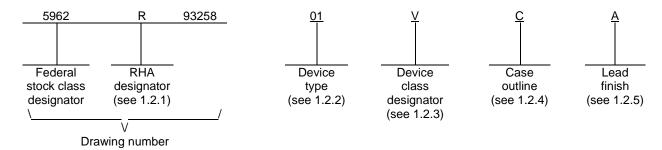
B Add ra C Add fra supply boiler C Chang Remo section E Addect F Drawi Delete	radiation hard footnote to the bly current an explate. – rrp nge to the ponoved acceler ion 4. – rrp ed subgroup wing updated at footnotes vise footnotes vi	dness require the supply volta d power supply st irradiation to ated aging ar to table IIA to reflect curr	age test ally rejecti test limits and dose i under grant rent requ	in table Add ca in section ratio s in tab rate built roup E e	e I. Upuse outlined in 1.3. o test in le I for rhout pend-points rrpothote s	line D. Add for table I IO, I IB provision int for comparison in the comparison in	Add tal	ble IIB. to the ate and I _{CC}	- rrp	DA	99-1 00-0 01-1 01-1 03-0 05-0	R-MO-E 1-16 05-05 0-17 1-15 03-11 09-07	DA)		R. Mo R. Mo R. Mo R. Mo R. Mo	ONNIN ONNIN ONNIN ONNIN ONNIN AFFLE	
B Add ra C Supply boiler D Chang Remo section E Added F Drawin G Delete These	radiation hard footnote to the oly current an explate. — rrp nge to the polyoved accelerion 4. — rrp ed subgroup wing updated ete footnote 2.	dness require the supply volta d power supply st irradiation to ated aging ar to table IIA to reflect curr	age test ally rejecti test limits and dose i under grant rent requ	Add ca in secti ion ratio s in tab rate bui	ise outling in 1.3 to test in 1.3 to	line D. Add for table I IO, I IB provision int for comparison in the comparison in	Add tal	ble IIB. to the ate and I _{CC}	- rrp		00-0 01-1 01-1 03-0 05-0	05-05 0-17 1-15 03-11			R. Mo R. Mo R. Mo R. Mo	NINNC NINNC NINNC NINNC	
C Supply boiler D Chang Remo section E Adder F Drawin G Delete These REV SHEET REV SHEET REV SHEET REV SHEET REV SHEETS PMIC N/A STANDAR	footnote to the bly current and erplate. — rrp ange to the ponoved acceler ion 4. — rrp ed subgroup wing updated ete footnote 2.	ne supply voltad power supplest irradiation tated aging are 4 to table IIA to reflect curr	age test oly rejecti test limits and dose i under gra rent requ	in section rations in table rate but roup E coup E	ion 1.3. test in test	. Add fin table Ino, IIB provision that for continuous for contin	, Ayo, ans in	e to the ate and I _{CC} class V.	· >-		01-1 01-1 03-0 05-0	0-17 1-15 03-11			R. Mo	NINNC NINNC NINNC	
C supply boiler D Chang Remo section E Added F Drawit G Delete These REV SHEET REV SHEET REV SHEET REV SHEET REV SHEET REV SHEETS PMIC N/A	oly current and erplate. – rrp Inge to the polyoved acceler ion 4. – rrp Inge to the polyoved acceler ion 4. – rrp Inge to the polyoved acceler ion 4. – rrp Inge to the polyoved acceler ion 4. – rrp Inge to the polyoved acceler in the polyoved acceler in the polyoved acceler in the polyoved acceleration i	d power supp st irradiation t ated aging ar 4 to table IIA to reflect curr	test limits and dose i under granter rent requ	s in tab rate bui	le I for rnout pend-points rrpotnote s	I _{IO} , I _{IB} , or ovision on the for o	, A _{VO} , ans in	and I _{CC}) .		01-1 03-0 05-0	1-15 03-11 09-07			R. Mo	NINNC NINNC	
B Added F Drawi G Delete These REV SHEET REV SHEET REV SHEET REV SHEETS PMIC N/A STANDAR	noved acceler ion 4. – rrp ed subgroup ving updated	ated aging ar 4 to table IIA to reflect curr	under greent requ	roup E e	end-poi	int for o	ns in device of	class V.			03-0)3-11)9-07			R. Mo	NINNC	
F Drawing Deleter These Standards STANDAR STANDAR	wing updated	to reflect curr	rent requ	uiremen	otnote (5/ from	Table I		- gt		05-0	9-07			R. M	NINNC	
REV SHEET REV SHEET REV SHEET REV SHEETS PMIC N/A	ete footnote 2	from section	1.3. De	elete fo	otnote :	5/ from	Table ro	l.									
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A	ete footnote <u>2</u> , se footnotes v	from section were incorrect	1.3. De tly addec	elete foo	otnote (<u>5</u> / from on C I	Table ro	I			10-0	04-22			C. S	AFFLE	
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STANDAR																	
SHEET REV STATUS OF SHEETS PMIC N/A STANDAR																	
REV STATUS OF SHEETS PMIC N/A STANDAR																	
OF SHEETS PMIC N/A STANDAR																	
PMIC N/A STANDAR		REV		G	G	G	G	G	G	G	G	G	G	G			<u> </u>
_	DD.	RICK C.	SHEET 1 2 3 PREPARED BY RICK C. OFFICER			3	4 5 6 7 8 9 10 11										
DRAWING	CUIT	RAJESH		HADIA			http://www.dscc.dla.mil										
THIS DRAWING IS AN FOR USE BY A DEPARTMENT AND AGENCIES CORPARTMENT OF D	\\/ΔII ∧D! ⊏	APPROVE MICHAE DRAWING	A. FR		DATE		HA OP	CROC RDEN ERAT	NED, ΓΙΟΝ	PRE	CISIO	ON, F	HIGH	SPE	ED, ()
AMSC N/A	ALL NTS OF THE	REVISION LEVEL								CAGE CODE 5962-93258							

1. SCOPE

- 1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.
 - 1.2 PIN. The PIN is as shown in the following example:



- 1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>
01	OP467	High speed, quad, operational amplifier

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as follows:

<u>Device class</u> <u>Device requirements documentation</u>

Vendor self-certification t

Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A

Q or V Certification and qualification to MIL-PRF-38535

1.2.4 <u>Case outline(s)</u>. The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14or CDFP2-F14	14	Flat pack
2	CQCC1-N20	20	Square leadless chip carrier

1.2.5 <u>Lead finish</u>. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

STANDARD
MICROCIRCUIT DRAWING

DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990

SIZE A		5962-93258
	REVISION LEVEL G	SHEET 2

M

1.3 Absolute maximum ratings. 1/

Supply voltage (V_{CC}) Differential input voltage $2/$ Input voltage $2/$ Output short-circuit duration Storage temperature range Lead temperature (soldering, 60 seconds) Junction temperature (T_J) Thermal resistance, junction-to-case (θ_{JC}) Thermal resistance, junction-to-ambient (θ_{JA}): Case C Case D	±26 V ±18 V Limited -65°C to +175°C +300°C -65°C to +175°C See MIL-STD-1835 94°C/W 140°C/W
Case D Case 2	

1.4 Recommended operating conditions.

Supply voltage (V _{CC})	±15 V
Ambient operating temperature range (T _A)	-55°C to +125°C

1.5 Radiation features.

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at https://assist.daps.dla.mil/quicksearch/ or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions specified in MIL-STD-883, method 1019, condition A.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-93258
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990		REVISION LEVEL G	SHEET 3

^{1/} Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

^{2/} For supply voltages less than \pm 18 V, the absolute maximum input voltage is equal to the supply voltage.

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.
 - 3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.3 Radiation exposure circuit. The radiation exposure circuit shall be as specified on figure 2.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.
- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.
- 3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M.</u> For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 49 (see MIL-PRF-38535, appendix A).

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-93258
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990		REVISION LEVEL G	SHEET 4

TABLE I. Electrical performance characteristics.

Test	Symbol			Group A subgroups	Device type	Limits <u>3</u> /		Unit
						Min	Max	-
Input offset voltage	V _{IO}	V _{CC} = ±5 V		1	01		0.5	mV
				2, 3			1.0	
		V _{CC} = ±15 V		1	1		0.5	
				2, 3	1		1.0	
			M,D,P,L,R	1			1.5	
Input offset current	I _{IO}	V _{CC} = ±5 V, V	' _{CM} = 0 V	1	01		100	nA
				2, 3			150	
		V _{CC} = ±15 V, V _{CM} = 0 V		1			100	=
				2, 3		150		
			M,D,P,L,R	1			300	
Input bias current	I _{IB}	V _{CC} = ±5 V, V	' _{CM} = 0 V	1	01		600	nA
				2, 3	=		700	
		V _{CC} = ±15 V, V _{CM} = 0 V		1	=	600	600	
				2, 3			700	
			M,D,P,L,R	1	=		2000	
Common mode rejection ratio	CMRR	$V_{CC} = \pm 5 \text{ V},$ $V_{CM} = \pm 2 \text{ V}$	<u>4</u> /	1, 2, 3	01	76		dB
		V _{CC} = ±15 V, <u>4</u> /				80		
		$V_{CM} = \pm 12 \text{ V}$				00		
Large signal voltage gain	Avo	$V_{CC} = \pm 5 \text{ V}, \text{ R}$	$k_L = 2 k\Omega$	4	01	80		dB
				5, 6		74		
		$V_{CC} = \pm 15 \text{ V},$	$R_L = 2 k\Omega$	4		83		
				5, 6		77.5		
			M,D,P,L,R	4		63		
Output voltage swing	Vout	$V_{CC} = \pm 5 \text{ V, R}$	$R_L = 2 \text{ k}\Omega \frac{4}{}$	4, 5, 6	01	±3.0		V
		$V_{CC} = \pm 15 \text{ V},$	$R_L = 2 k\Omega \frac{4}{}$	4		±13		
				5, 6]	±12.9		

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-93258
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		G	5

TABLE I. Electrical performance characteristics - Continued

Test	Symbol	$\begin{array}{c} \text{Conditions} \underline{1}/\underline{2}/\\ \text{symbol} \\ -55^{\circ}\text{C} \leq \text{T}_{A} \leq +125^{\circ}\text{C}\\ \text{unless otherwise specified} \end{array}$		Group A subgroups	Device type	Limits 3/		Unit
						Min	Max	1
Supply current	Icc	$V_{CC} = \pm 5 \text{ V}, V_{OUT} = 0 \text{ V}$		1	01		10	mA
				2, 3			12]
		V _{CC} = ±15 V	, V _{OUT} = 0 V	1			10	
				2, 3			13	
			M,D,P,L,R	1			11	
Power supply rejection ratio	PSRR	V _{CC} = ±4.5 V	′ to ±5.5 V <u>4</u> /	1	01	92		dB
				2, 3		83		
		V _{CC} = ±4.5 V	′ to ±18 V <u>4</u> /	1		96		
				2, 3		86		
Input offset voltage drift	TC _{VIO}	$V_{CC} = \pm 15 \text{ V}, \underline{4}/$ $T_A = +125^{\circ}\text{C}, -55^{\circ}\text{C}$		8	01		5	μV/°C
Gain bandwidth product	GBWP	$V_{CC} = \pm 5 \text{ V}, A_V = +1, \underline{4}/$ $C_L = 30 \text{ pF}, T_A = +25 ^{\circ}\text{C}$		7	01	16		MHz
		$V_{CC} = \pm 15 \text{ V}$ $C_L = 30 \text{ pF}, 7$, A _V = +1, <u>4</u> /			21		
Slew rate	SR	$V_{CC} = \pm 5 \text{ V},$ $V_{IN} = 5 \text{ V ste}$ $A_{V} = +1, R_{L} =$	p, = 2 kΩ,	7	01	85		V/μs
		$C_L = 30 \text{ pF}, 7$						
		$V_{CC} = \pm 15 \text{ V}$	$A_{V} = +1, \ \underline{4}$			125		
		V _{IN} = 10 V st	ep, $R_L = 2 kΩ$,					
		C _L = 30 pF, 7	T _A = +25°C					
Settling time	ts	$V_{CC} = \pm 15 \text{ V}_{IN}$ $V_{IN} = 10 \text{ V st}$ of the final va	ep to 0.01%	9	01		300	ns
		T _A = +25°C						

^{1/2} RHA devices supplied to this drawing will meet all levels M, D, P, L, R of irradiation. However, this device is only tested at the 'R' level. Pre and Post irradiation values are identical unless otherwise specified in table I. When performing post irradiation electrical measurements for any RHA level, $T_A = +25^{\circ}C$.

4/ This parameter is not tested post-irradiation.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-93258
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		G	6

These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions specified in MIL-STD-883, method 1019, condition A.

^{3/} The limiting terms "min" (minimum) and "max" (maximum) shall be considered to apply to magnitudes only. Negative current shall be defined as conventional current flow out of a device terminal.

Device type	01	
Case outlines	C and D	2
Terminal number	Terminal s	symbol
1	OUTPUT A	NC
2	-INPUT A	OUTPUT A
3	+INPUT A	-INPUT A
4	+V _{CC}	+INPUT A
5	+INPUT B	NC
6	-INPUT B	+Vcc
7	OUTPUT B	NC
8	OUTPUT C	+INPUT B
9	-INPUT C	-INPUT B
10	+INPUT C	OUTPUT B
11	-Vcc	NC
12	+INPUT D	OUTPUT C
13	-INPUT D	-INPUT C
14	OUTPUT D	+INPUT C
15		NC
16		-Vcc
17		NC
18		+INPUT D
19		-INPUT D
20		OUTPUT D

NC = No connection

FIGURE 1. Terminal connections.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-93258
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990		REVISION LEVEL G	SHEET 7

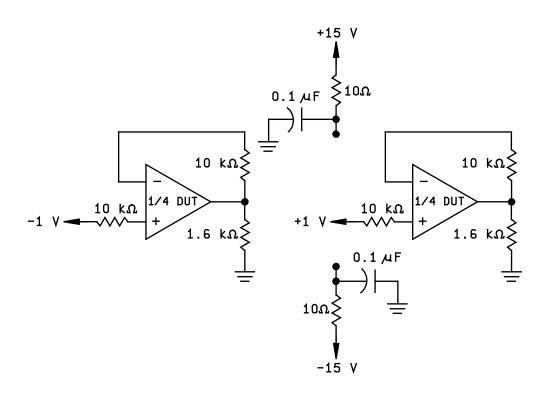


FIGURE 2. Radiation exposure circuit.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-93258
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990		REVISION LEVEL G	SHEET 8

4. VERIFICATION

- 4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.
 - 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition B. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.
- 4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
 - 4.4.1 Group A inspection.
 - a. Tests shall be as specified in table IIA herein.
 - b. Subgroups 10 and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-93258
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		G	9

TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with	Subgr (in accord	•
	MIL-STD-883, method 5005, table I)	MIL-PRF-38	535, table III)
	Device	Device	Device
	class M	class Q	class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1,2,3,4,5,6 <u>1</u> /	1,2,3,4,5,6 <u>1</u> /	1,2,3, <u>1</u> / <u>2</u> / 4,5,6
Group A test requirements (see 4.4)	1,2,3,4,5,6,7,8,9	1,2,3,4,5,6, 7,8,9	1,2,3,4,5,6, 7,8,9
Group C end-point electrical parameters (see 4.4)	1	1	1 <u>2</u> /
Group D end-point electrical parameters (see 4.4)	1	1	1
Group E end-point electrical parameters (see 4.4)			1,4

^{1/} PDA applies to subgroup 1. Exclude delta from PDA.

TABLE IIB. Burn-in and operating life test delta parameters. $T_A = +25^{\circ}C$. 1/2/

Parameter	Device type	End-Point		Delta	Unit
		Min	Max	Max	Offic
V _{IO}	01		0.5	±0.2	mV
I _{IB}	01		600	±250	nA

^{1/} Deltas are performed at room temperature.

- 4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition B. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - b. $T_A = +125$ °C, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-93258
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		G	10

^{2/} Delta limits as specified in table IIB shall be required where specified, and the delta limits shall be computed with reference to the zero hour electrical parameters (see table I).

^{2/ 240} hour burn-in and 1,000 hour operating group C life test.

- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).
 - a. End-point electrical parameters shall be as specified in table IIA herein.
 - b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at TA = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.
- 4.4.4.1 <u>Total dose irradiation testing</u>. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019 condition A and as specified herein.
 - 5. PACKAGING
- 5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.
 - 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.
 - 6.1.2 Substitutability. Device class Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus (DSCC) when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0547.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.
 - 6.6 Sources of supply.
- 6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.
- 6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-93258
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		G	11

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 10-04-22

Approved sources of supply for SMD 5962-93258 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DSCC maintains an online database of all current sources of supply at http://www.dscc.dla.mil/Programs/Smcr/.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-9325801MCA	24355 (2)	OP467AY/883
5962-9325801M2A	24355 (2)	OP467ARC/883
5962-9325801VCA	24355 (4)	OP467AY/QMLV
5962-9325801V2A	24355 (4)	OP467ARC/QMLV
5962R9325801VDA	24355 (4)	OP467AM/QMLR
5962R9325801VCA	24355 (4)	OP467AY/QMLR

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- <u>2</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE <u>number</u>	Vendor name <u>and address</u>
24355 (2)	Analog Devices Route 1 Industrial Park P.O. Box 9106 Norwood, MA 02062 Point of contact: 804 Woburn Street Wilmington, MA 01887-3462
24355 (4)	Analog Devices Route 1 Industrial Park P.O. Box 9106 Norwood, MA 02062

Point of contact: 7910 Triad Center Drive

Greensboro, NC 27409-9605

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001:
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина,

дом 2, корпус 4, литера А.